

Fig. 1 TG and isothermal TG (inset) analysis of the novel Sn precursor. Heating rates of  $5 \text{ K min}^{-1}$  were applied in all experiments. Averaged evaporation rates were calculated after equilibration of evaporation for 170 min. All experiments were conducted at room pressure.

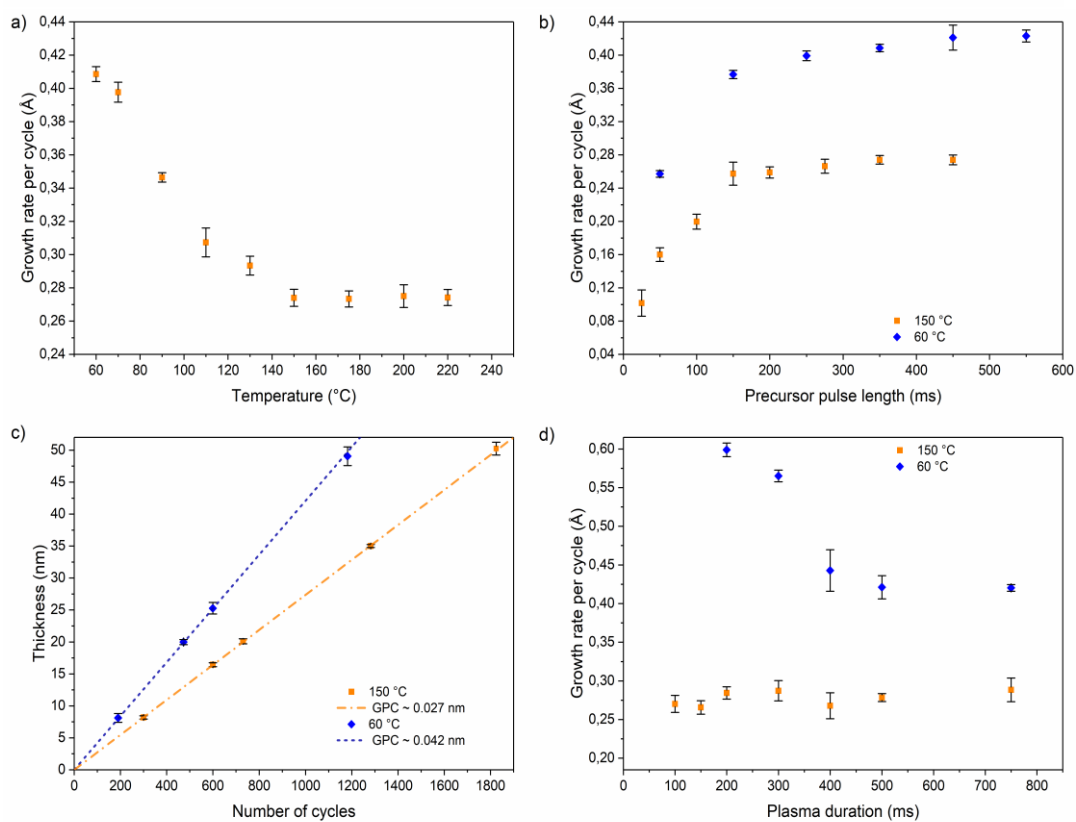


Fig. 2 Growth characteristics: (a) ALD window, (b) saturation study with varying precursor pulse length for both temperatures, (c) thickness of thin films vs. applied number of cycles at 60 °C and 150 °C, and (d) growth per cycle under variation of plasma pulse length.